

FEATURES

- Ø 1.60 mm active area
- Small gap
- Low dark current
- High resolution

DESCRIPTION

4 X 0.49 mm² Low Dark Current Quadrant Photodiode with P on N construction and 20 µm gaps. Hermetically packaged in a TO-5 with a clear borosilicate glass window cap.

APPLICATIONS

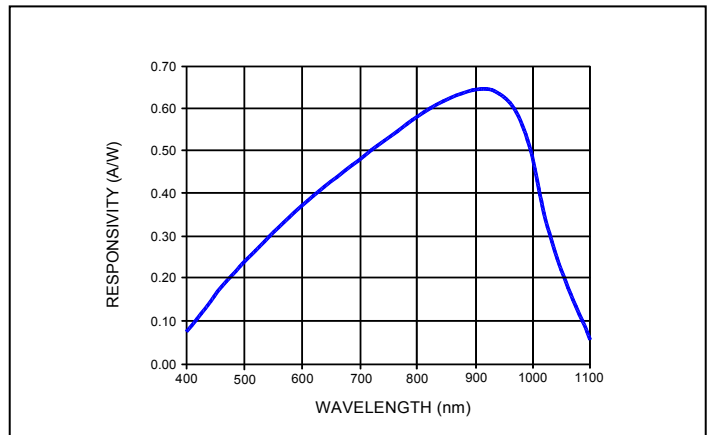
- Laser beam position sensor
- Autocollimators
- Optical tweezers
- Ellipsometers



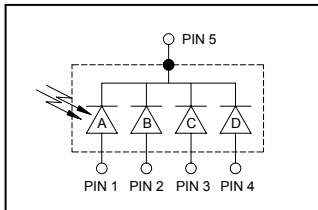
ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-55	+125	°C
T _{OP}	Operating Temp	-40	+100	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _(PEAK)	Peak DC Current	-	10	mA

SPECTRAL RESPONSE



SCHEMATIC



ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _D	Dark Current*	V _R = 10 V	---	0.1	---	nA
C	Capacitance*	V _R = 10 V	---	---	2.0	pF
	Responsivity	V _R = 0 V; λ = 633 nm	---	0.40	---	A/W
		V _R = 0 V; λ = 900 nm	---	0.64	---	
V _{BR}	Breakdown Voltage	I _R = 10 µA	---	15	---	V
t _r	Rise Time	V _R = 10 V; λ = 850 nm; R _L = 50 Ω	---	20	---	ns
	Uniformity of Sensitivity	V _R = 10 V; λ = 880 nm	---	±1	±2	%

* per element

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

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